ISHA

New Product

SS1P3 & SS1P4

Vishay General Semiconductor

High Current Density Surface Mount Schottky Barrier Rectifiers

FEATURES

- Very low profile typical height of 1.0 mm
- Ideal for automated placement
- · Low forward voltage drop, low power losses
- High efficiency
- · Low thermal resistance
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

TYPICAL APPLICATIONS

For use in low voltage high frequency inverters, freewheeling, dc-to-dc converters, and polarity protection applications.

(Note: These devices are not Q101 qualified.)

MECHANICAL DATA

Case: DO-220AA (SMP)

Epoxy meets UL 94V-0 flammability rating

Terminals: Matte tin plated leads, solderable per J-STD-002 and JESD22-B102

E3 suffix for consumer grade, meets JESD 201 class 1A whisker test

Polarity: Color band denotes the cathode end

| MAXIMUM RATINGS ($T_A = 25 \degree C$ unless otherwise noted) | | | | | |
|--|-----------------------------------|---------------|-------|------|--|
| PARAMETER | SYMBOL | SS1P3 | SS1P4 | UNIT | |
| Device marking code | | 13 14 | | | |
| Maximum repetitive peak reverse voltage | V _{RRM} | 30 | V | | |
| Maximum average forward rectified current (Fig. 1) | I _{F(AV)} | 1.0 | | А | |
| Peak forward surge current 10 ms single half sine-wave superimposed on rated load | I _{FSM} | 30 | | А | |
| Non-repetitive avalanche energy at I_{AS} = 1.5 A, L = 10 mH, T_J = 25 \ ^{\circ}C | E _{AS} | 10 | | mJ | |
| Voltage rate of change (rated V _R) | dV/dt | 10 000 | | V/µs | |
| Operating junction and storage temperature range | T _J , T _{STG} | - 55 to + 150 | | °C | |

ELECTRICAL CHARACTERISTICS (T_A = 25 °C unless otherwise noted)

| PARAMETER | TEST CONDITIONS | | SYMBOL | SS1P3 | SS1P4 | UNIT |
|--|--|---|----------------|--------------|--------------|----------|
| Maximum instantaneous forward voltage ⁽¹⁾ | l _F = 1.0 A l _F = 1.0 A | T _J = 25 °C T _J = 125 °C | V _F | 0.50 0.40 | 0.53 0.45 | V |
| Maximum reverse current at rated $V_R^{(2)}$ | | T _J = 25 °C T _J = 125 °C | I _R | 150 15 | | μA mA |
| Typical junction capacitance | 4.0 V, 1 MHz | | CJ | 70 | | pF |

Notes:

(1) Pulse test: 300 µs pulse width, 1 % duty cycle

(2) Pulse test: Pulse width \leq 40 ms

RoHS COMPLIANT

| PRIMARY CHARACTERISTICS | | | | |
|-------------------------|----------------|--|--|--|
| I _{F(AV)} | 1 A | | | |
| V _{RRM} | 30 V, 40 V | | | |
| I _{FSM} | 30 A | | | |
| E _{AS} | 10 mJ | | | |
| V _F | 0.40 V, 0.45 V | | | |
| T _J max. | 150 °C | | | |

eSMP[™] Series



DO-220AA (SMP)

SS1P3 & SS1P4



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| THERMAL CHARACTERISTICS (T _A = 25 °C unless otherwise noted) | | | | | |
|--|--|-----------------|--|------|--|
| PARAMETER | SYMBOL SS1P3 SS1P4 | | | UNIT | |
| Typical thermal resistance ⁽¹⁾ | R _{θJA} R _{θJL} R _{θJC} | 105 15 25 | | °C/W | |

Note:

(1) Thermal resistance from junction to ambient and junction to lead mounted on P.C.B. with 5.0 x 5.0 mm copper pad areas $R_{\theta JL}$ is measured at the terminal of cathode band. $R_{\theta JC}$ is measured at the top centre of the body

| ORDERING INFORMATION (Example) | | | | |
|--------------------------------|-----------------|------------------------|---------------|------------------------------------|
| PREFERRED P/N | UNIT WEIGHT (g) | PREFERRED PACKAGE CODE | BASE QUANTITY | DELIVERY MODE |
| SS1P3-E3/84A | 0.024 | 84A | 3000 | 7" diameter plastic tape and reel |
| SS1P3-E3/85A | 0.024 | 85A | 10 000 | 13" diameter plastic tape and reel |

RATINGS AND CHARACTERISTICS CURVES

(T_A = 25 °C unless otherwise noted)

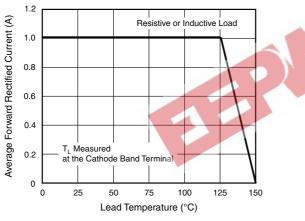


Figure 1. Maximum Forward Current Derating Curve

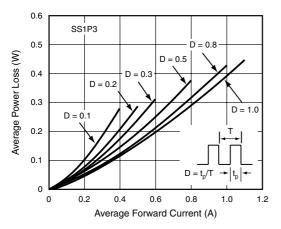


Figure 2. Forward Power Loss Characteristics

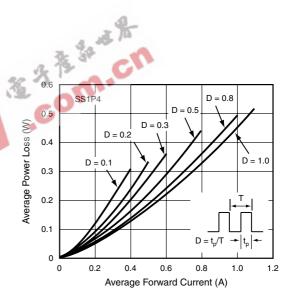
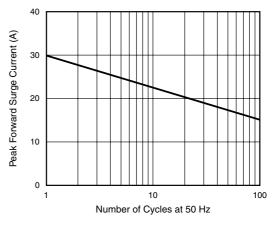


Figure 3. Forward Power Loss Characteristics





For technical questions within your region, please contact one of the following: PDD-Americas@vishay.com, PDD-Asia@vishay.com, PDD-Europe@vishay.com



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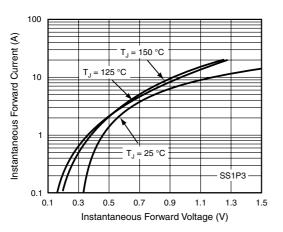


Figure 5. Typical Instantaneous Forward Characteristics

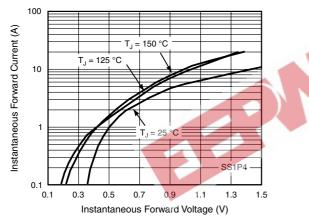


Figure 6. Typical Instantaneous Forward Characteristics

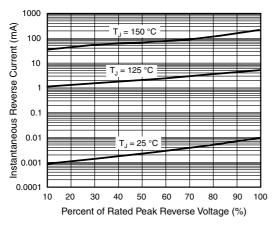


Figure 7. Typical Reverse Leakage Characteristics

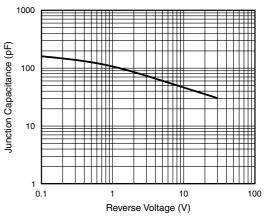


Figure 8. Typical Junction Capacitance

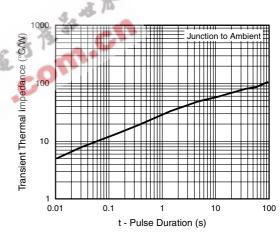


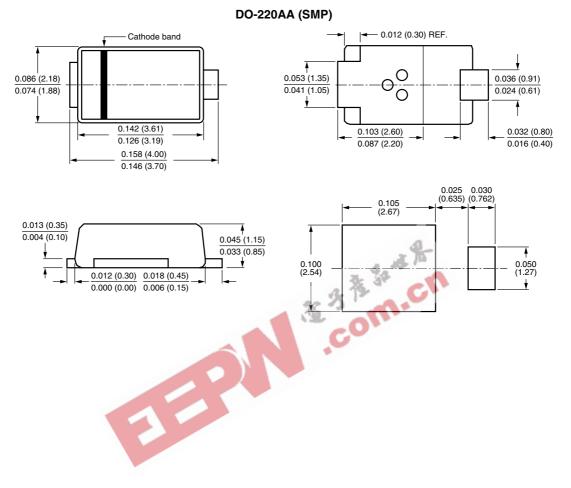
Figure 9. Typical Transient Thermal Impedatnce

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PACKAGE OUTLINE DIMENSIONS in inches (millimeters)





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